CLAIMS

1. Integrated circuit including at least two circuit components (1, 2), which are formed on a semiconductor substrate (13) of the first conductivity type and which each have a self-contained supply voltage system, and including at least one coupling circuit which connects the same potentials (Vss1, Vss2; Vcc1, Vcc2) of the two supply voltage systems so as to intercept voltage spikes, characterized in that the coupling circuit includes at least one transistor (T1, T2, T3) with a base (20, 21, 22) of the first conductivity type, and a collector (15, 16, 17, 18) and emitter (15, 16, 17, 18) of a second conductivity type, the base of which is connected through a resistance (R) to the potentials (Vss1, Vss2) of the two supply voltage systems, and the collector and emitter of which are connected directly to one of these potentials.

2. The integrated circuit of claim 1, wherein the base (20, 21, 22) of the transistor (T1, T2, T3) is a region of the substrate (13), and that the resistance (R) is the intrinsic resistance of the substrate (13) between the base (20, 21, 22) and a contact doping zone (14, 19) metallically connected to the collector or emitter.

3. The integrated circuit of claim 2, wherein the collector and emitter of the transistor are symmetrical.

4. The integrated circuit of claim 3, wherein the coupling circuit includes a plurality of transistors (T1, T2, T3) connected in parallel between the power supply potentials (Vss1, Vss2).

5. The integrated circuit of claim 4, wherein the transistors comprise a plurality of doping zones (15, 16, 17, 18) of the second conductivity type, which doping zones are alternately connected to the first (Vss1) or the second (Vss2) of the two power supply potentials.

6. The integrated circuit of claim 5, wherein the doping zones (15, 16, 17, 18) are arranged in an equidistant configuration.

7. The integrated circuit of claim 6, wherein the doping zones (15, 16, 17, 18) of the second conductivity type are extended transversely relative to the series.

8. The integrated circuit of claim 7, wherein the contact doping zones (14, 19) are located at the ends of the series.

9. The integrated circuit of claim 8, wherein each contact doping zone (14, 19) in the series is adjacent to a doping zone (15, 18) of the second conductivity type which is metallically connected to the zone.

10. The integrated circuit of claim 9, wherein the number of doping zones (15, 16, 17, 18) of the second conductivity type is an even number.

11. The integrated circuit of claim 10, wherein the circuit has four doping zones (15, 16, 17, 18) of the second conductivity type.

12. The integrated circuit of claim 11, wherein the at least one transistor is surrounded by a shielding doping zone (23) of the second conductivity type.

13. The integrated circuit of claim 12, wherein the shielding doping zone (23) is biased in the nonconducting direction.

14. The integrated circuit of claim 12, the shielding doping zone (23) extends in an annular configuration along the surface of the substrate (13).

15. The integrated circuit of claim 14, wherein a highly doped contact zone (25) is formed in the shielding doping zone (23).

16. The integrated circuit of claim 15, wherein the contact zone (25) includes two islands, each of which is conductively connected to one of the potentials (Vss1, Vss2) of the two supply voltage systems.

17. The integrated circuit of claim 15, wherein the contact doping zones (14, 19) are formed on the shielding doping zone (23).